

NTE2547 (NPN) & NTE2548 (PNP) Silicon Complementary Transistors Darlington Driver TO-220 Full Pack

Features:

- High DC Current Gain
- High Current Capacity and Wide ASO
- Low Saturation Voltage

Applications:

- Motor Drivers
- Printer Hammer Drivers
- Relay Drivers
- Voltage Regulator Control

Absolute Maximum Ratings: (T _A = +25°C unless otherwise specified)
Collector to Base Voltage, V _{CBO}
Collector to Emitter Voltage, V _{CEO}
Emitter to Base Voltage, V _{EBO} 6V
Collector Current, I _C
Continuous
Peak
Collector Dissipation, P _C
$T_A = +25^{\circ}\text{C}$
$T_C = +25^{\circ}C$
Operating Junction Temperature, T _J +150°C
Storage Temperature Range, T _{stg} –55° to +150°C

Electrical Characteristics: (T_A = +25°C, Note 1 unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector Cutoff Current	I _{CBO}	$V_{CB} = 80V, I_{E} = 0$	_	_	0.1	mA
Emitter Cutoff Current	I _{EBO}	$V_{EB} = 5V, I_{C} = 0$	-	_	3.0	mA
DC Current Gain	h _{FE}	$V_{CE} = 3V$, $I_C = 4A$	1500	4000		
Transition Frequency	f _T	$V_{CE} = 5V$, $I_C = 4A$	_	20	_	MHz

Note 1. For NTE2548 (PNP), the polarity is reversed.



<u>Electrical Characteristics (Cont'd):</u> $(T_A = +25^{\circ}C, \text{ Note 1 unless otherwise specified)}$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector-to-Emitter Saturation Voltage NTE2547	V _{CE(sat)}	I _C = 4A, I _B = 8mA	_	0.9	1.5	V
NTE2548			_	1.0	1.5	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C = 4A, I _B = 8mA	_	_	2.0	V
Collector-Base Breakdown Voltage	V _{(BR)CBO}	$I_C = 5mA, I_E = 0$	110	_	_	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_C = 50$ mA, $R_{BE} = \infty$	100	_	_	V
Turn-On Time NTE2547	t _{on}	$I_{C} = 500I_{B1} = -500I_{B2} = 4A,$	_	0.6	_	μS
NTE2548		$V_{CC} = 50V, R_L = 12.5\Omega$	_	0.7	_	μS
Storage Time NTE2547	t _{stg}		_	4.8	_	μS
NTE2548			_	1.4	_	μS
Fall Time NTE2547	t _f		_	1.6	_	μs
NTE2548			_	1.5	_	μS

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